

Mayer, Fortkort & Williams, PC
251 North Avenue West. 2nd Floor
Westfield, NJ 07090

Fax Cover Sheet

DATE:	July 2, 2003	PAGES:	<u>11 (eleven) w/cover</u>
TO:	Examiner Tan N. Tran GAU 2826	PHONE:	(703) 305-3362
		FAX:	(703) 872-9319
FROM:	Karin L. Williams Mayer, Fortkort & Williams, PC	PHONE:	(908) 518-7700
		FAX:	(908) 518-7795

Message

DOCKET GS 150

Please see attached: Response After Final Rejection

FAX RECEIVED

JUL 02 2003

TECHNOLOGY CENTER 2800

Response after Final Rejection
Expedited Handling Requested - GAU 2826

CONFIDENTIALITY NOTICE

This facsimile transmission is intended only for the use of the addressee and may contain confidential information which is protected by the attorney/client privilege. If you are not the recipient, you are hereby notified that any disclosure, copying, distribution or the taking of any action in reliance on the contents of this information is strictly prohibited. If you have received this communication in error, please notify us immediately by telephone to arrange for its return.

Response
710
Patent
10/010,484

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hshieh et al.
Serial No.: 10/010,484
Filed: November 20, 2001
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure
Art Unit: 2826
Examiner: Tan N. Tran
Docket No.: GS 150

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

RESPONSE AFTER FINAL REJECTION

FAX RECEIVED
JUL 02 2003
TECHNOLOGY CENTER 2800

Sir:

In response to the final Office Action dated May 3, 2003 (Paper No. 10), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.